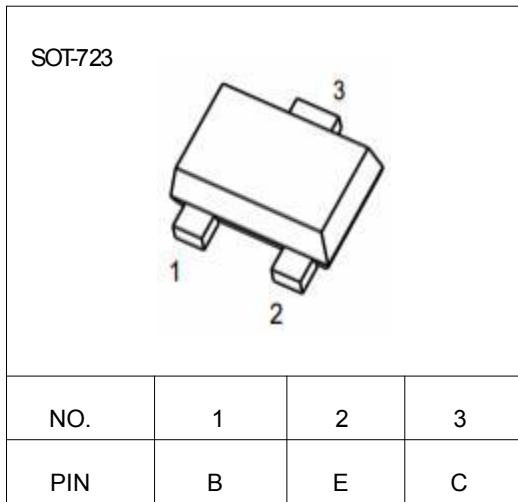


■ FEATURES

- Complement to MMBT3906M
- Collector-Emitter Voltage : $V_{ce0}=40V$
- Collector Dissipation : $P_c=100mW(T_a=25^{\circ}C)$

■ MARKING:1N

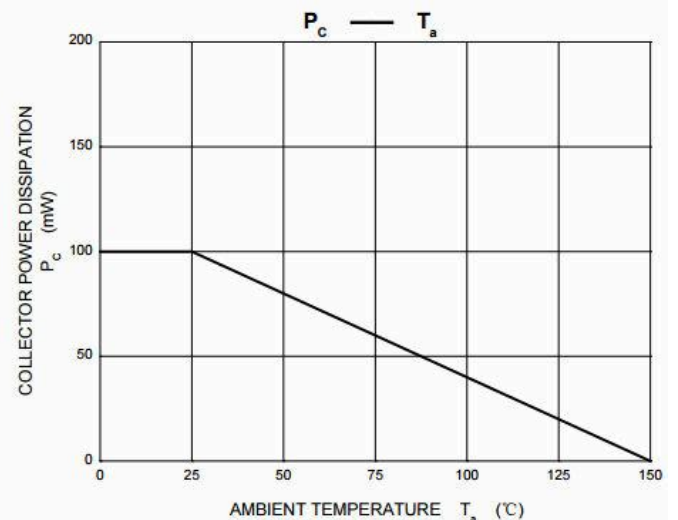
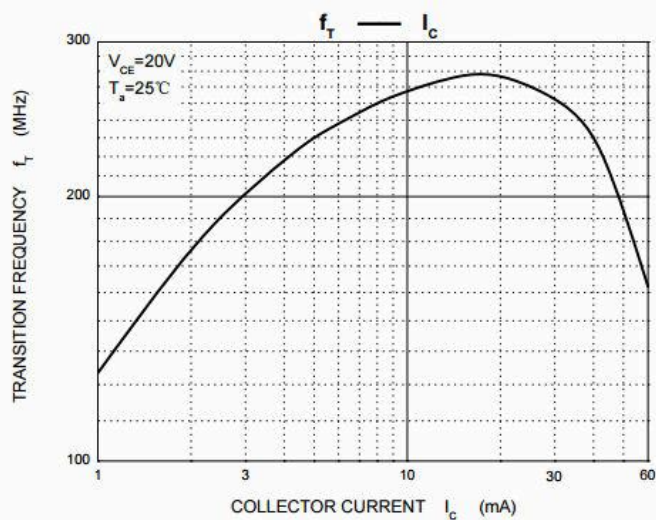
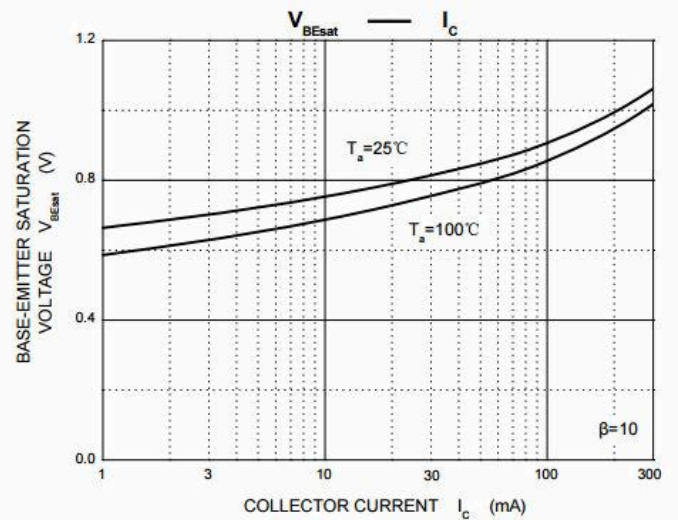
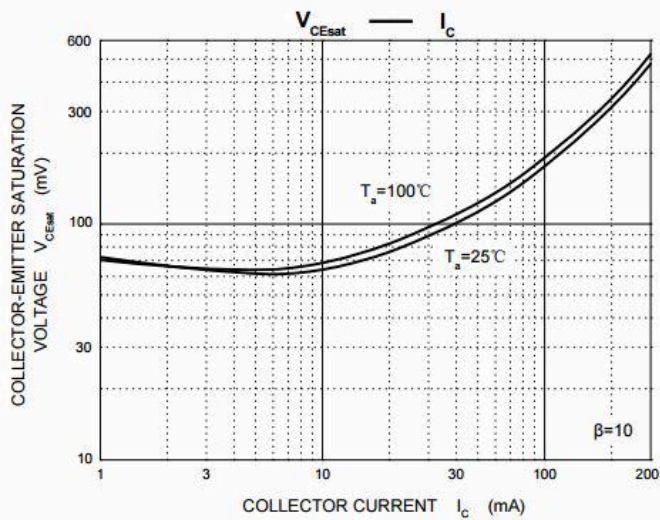
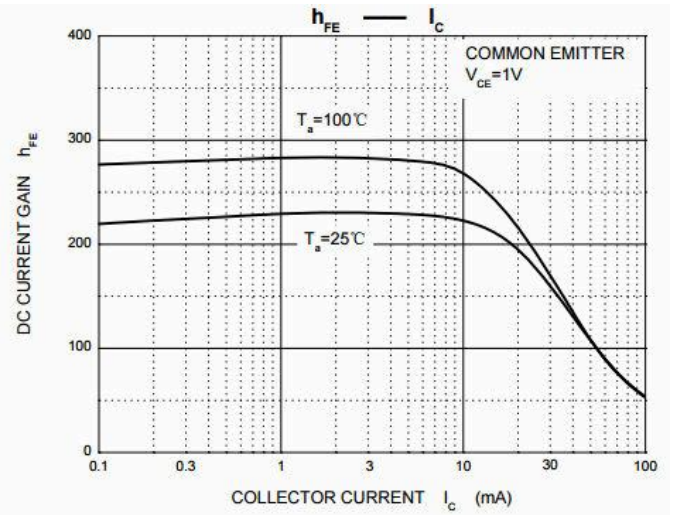
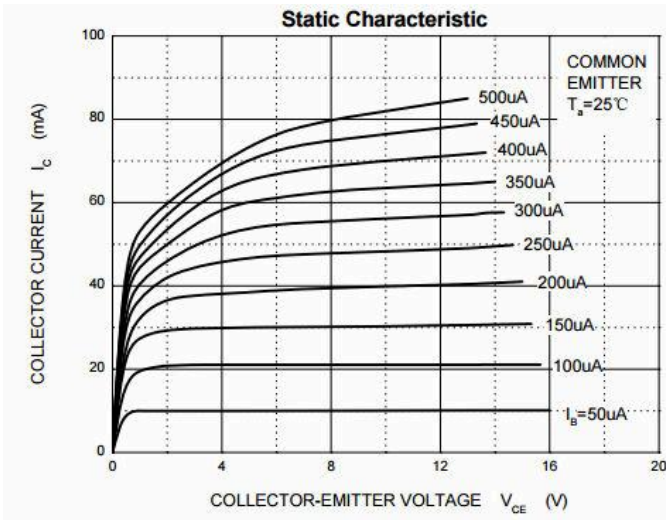


■ Absolute Maximum Ratings ($T_{amb}=25^{\circ}C$)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{cbo}	60	V
Collector-Emitter Voltage	V_{ceo}	40	V
Emitter-Base Voltage	V_{ebo}	6	V
Collector Current	I_c	200	mA
Collector Dissipation	P_c	100	mW
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature	T_{stg}	-55~150	$^{\circ}C$

■ Electrical Characteristics ($T_{amb}=25^{\circ}C$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{cbo}	$I_c=10\mu A, I_e=0$	60			V
Collector-Emitter Breakdown Voltage	BV_{ceo}	$I_c=1mA, I_b=0$	40			V
Emitter-Base Breakdown Voltage	BV_{ebo}	$I_e=10\mu A, I_c=0$	6			V
Collector Cutoff Current	I_{cex}	$V_{ce}=30V, V_{eb}=3V$			50	nA
Emitter Cutoff Current	I_{ebo}	$V_{eb}=5V, I_c=0$			100	nA
DC Current Gain	H_{fe1}	$V_{ce}=1V, I_c=0.1mA$	40			
DC Current Gain	H_{fe2}	$V_{ce}=1V, I_c=1mA$	70			
DC Current Gain	H_{fe3}	$V_{ce}=1V, I_c=10mA$	100		300	
DC Current Gain	H_{fe4}	$V_{ce}=1V, I_c=50mA$	60			
Collector-Emitter Saturation Voltage	$V_{ce(sat)}$	$I_c=10mA, I_b=1mA$			0.2	V
Collector-Emitter Saturation Voltage	$V_{ce(sat)}$	$I_c=50mA, I_b=5mA$			0.3	V
Base-Emitter Saturation Voltage	$V_{be(sat)}$	$I_c=10mA, I_b=1mA$			0.85	V
Base-Emitter Saturation Voltage	$V_{be(sat)}$	$I_c=50mA, I_b=5mA$			0.95	V
Output Capacitance	C_{ob}	$V_{cb}=5V, I_e=0, f=1MHz$			4	pF
Current Gain-Bandwidth Product	f_T	$V_{ce}=20V, I_c=10mA, f=100MHz$	300			MHz



■ SOT-723 PACKAGE OUTLINE DIMENSIONS

